## HIGH FREQUENCY CHARACTERISTICS AND MAGNETIC PROPERTIES OF CoFeAIO/NATIVE OXIDE MULTILAYER FILMS

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Multilayers soft FeCoAlO/Native-Oxides structure films with excellent soft magnetic properties and ultrahigh frequency characteristics were investigated. Multilayers consisting of discontinuous CoFeAlO layers with native-oxides surfaces were fabricated using  $Co_{30}Fe_{70}$  + Al chips alloys targets with a purity of 99.95%. The background pressure was <  $2.0 \times 10^{-7}$  Torr. CoFeAlO films with nominal thickness of about 150 Å were deposited onto Si (100) wafer through RF reactive magnetron sputtering in Ar atmosphere. Each layer was exposed for 15 s in situ to an  $O_2$  flow of 2 sccm, yielding a

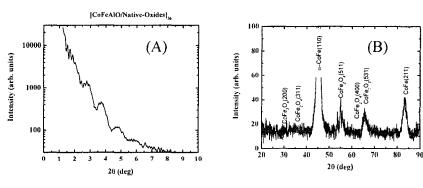


Figure 1. X-ray diffraction patterns of [CoFeAlO (150 Å )/Native-Oxides]<sub>36</sub> multilayers thin films. (A) low angle; (B)  $2\theta$ - $\theta$ 

 $P_{O_2}$  of about  $5\times10^{-5}$  Torr. The  $O_2$  flow was then terminated, followed by a pause for 2 minutes before depositing the next layers, which allowed the  $O_2$  pressure to drop to its BP This was repeated until the desired film thickness was reached. The notation [CoFeAlO(150 Å)/oxide]<sub>n</sub> denotes a structure in which each of the n unit layers consists of nominal thickness 150 Å of  $(\text{Co}_x\text{Fe}_{1-x})_n$  which has been oxidized using the prior procedure. Samples were characterized structurally by x-ray diffractometer (XRD) and transmission electron microscopy (TEM). The results were shown in the figure 1. The soft magnetic properties  $(4\pi M_s \sim 17 \text{ kG}, H_c < 0.3 \text{ Oe}, H_k \sim 50 \text{ Oe})$  of the multilayers films were measured by a VSM, as shown in figure 2. The electrical properties of the thin films  $(\rho)$  was measured using a four-point probe method. The  $\rho$  of [CoFeAlO(150 Å)/oxide]<sub>n</sub> films exceeds  $10^3 \mu\Omega$  cm, which is comparable to values obtained in CoFe-TM-O or metal/insulator [1-3] composites multilayers. The CoFeAlO/Native-Oxides multilayers films show  $\mu_{\text{eff}} > 1000$ , which is flat up to 2 GHz. The film can be a strong candidate for the materials used under ultra high frequency in GHz range.

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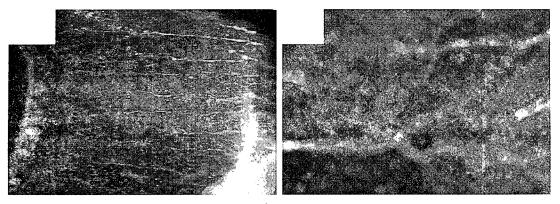


Figure 2. TEM micrograph of [CoFeAlO (150 Å )/Native-Oxides] $_{36}$  multilayers thin films. (A) Cross-sectional TEM; (B) In-plane TEM

## References

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